In th Specification

Paragraph 0018 on page 4 has been amended as follows:

Further advantageous refinements and developments of the invention emerge from the subclaims and from the exemplary embodiments described in principle below with reference to the drawing, in which:

figure 1 shows a basic representation of a faceted mirror according to the invention, arranged in an EUV lighting system for microlithography,

~~figure 2 shows a first method of production for a faceted mirror,~~

figure 2a shows a first method of production for a faceted mirror,

figure 2b shows a side sectional view of the faceted mirror of figure 2a taken along the line 2b-2b,

figure 3 shows a second method of production for a faceted mirror, and

figure 4 shows a basic body for a faceted mirror with reinforcements in a honeycomb structure and with cooling channels.

Paragraph 0020 on page 5 has been amended as follows:

The production of the faceted mirror 1 with correspondingly high precision and homogeneous or as-desired illumination takes place according to ~~figure 2~~ figures 2a and 2b on a basic body 8. The basic body 8 may be formed for

example by galvanic means, its functional surface corresponding with respect to curvature and position to the requirements which the finished faceted mirror 1 has to meet. Only the surface quality is still lacking. The surface quality is then realized by individual mirror elements 9 as optical elements.

C2 end

Paragraph 0023 on page 6 has been amended as follows:

Galvanoplastic processes are generally known, for which reason they are not discussed in any more detail here. In principle, this takes place by the mirror elements 9 being brought into their position on the basic body 8 and the entire unit then being cathodically connected in an electrolytic bath and the desired material, for example Cu or Ni, being used as the anode, so that the parts can grow together to form one unit. In this way, for example, the growing on of an intermediate layer 10, such as a copper layer of any desired thickness can be achieved. Additionally, as is known for galvanoplastic processing, figure 2b illustrates mirror elements 9 may be partially covered by a protection layer 30 (indicated by dashed lines) before the galvanoplastic processing to prevent the intermediate layer 10 being formed over selected portions of the mirror elements 9 during the galvanoplastic process.

C3